

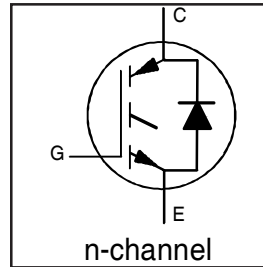
# IRG4BC20FDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST  
SOFT RECOVERY DIODE

Fast CoPack IGBT

**Features**

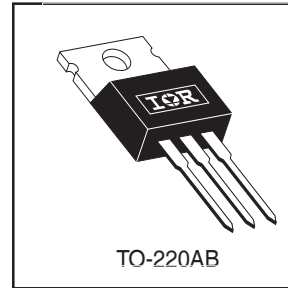
- Fast: optimized for medium operating frequencies ( 1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free



$V_{CES} = 600V$   
 $V_{CE(on) typ.} = 1.66V$   
@  $V_{GE} = 15V, I_C = 9.0A$

**Benefits**

- Generation -4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs. Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	16	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	9.0	
$I_{CM}$	Pulsed Collector Current ①	64	
$I_{LM}$	Clamped Inductive Load Current ②	64	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
$I_{FM}$	Diode Maximum Forward Current	32	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	2.1	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	80	
$Wt$	Weight	---	2 (0.07)	---	g (oz)

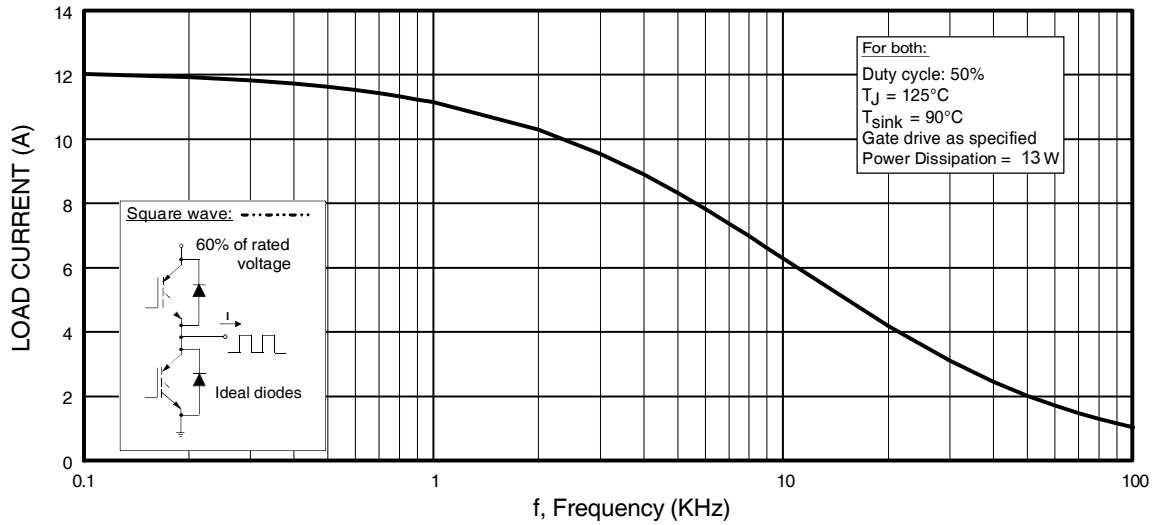
# IRG4BC20FDPbF

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

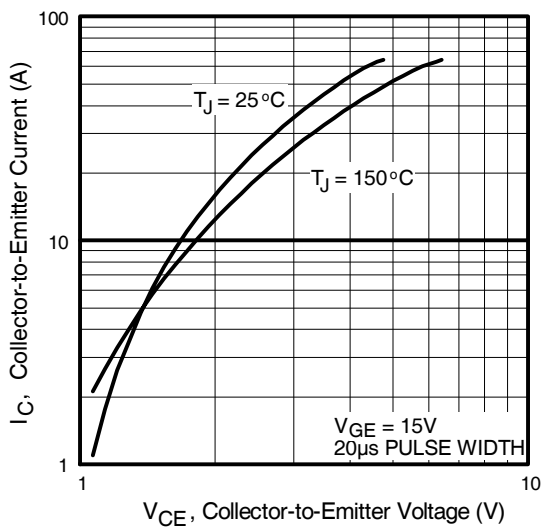
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.72	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.66	2.0	V	I <sub>C</sub> = 9.0A V <sub>GE</sub> = 15V
		—	2.06	—		I <sub>C</sub> = 16A See Fig. 2, 5
		—	1.76	—		I <sub>C</sub> = 9.0A, T <sub>J</sub> = 150°C
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	—	6.0		V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
g <sub>fe</sub>	Forward Transconductance <sup>④</sup>	2.9	5.1	—	S	V <sub>CE</sub> = 100V, I <sub>C</sub> = 9.0A
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	—	250	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V
		—	—	1700		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 150°C
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.4	1.7	V	I <sub>C</sub> = 8.0A See Fig. 13
		—	1.3	1.6		I <sub>C</sub> = 8.0A, T <sub>J</sub> = 150°C
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V

## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

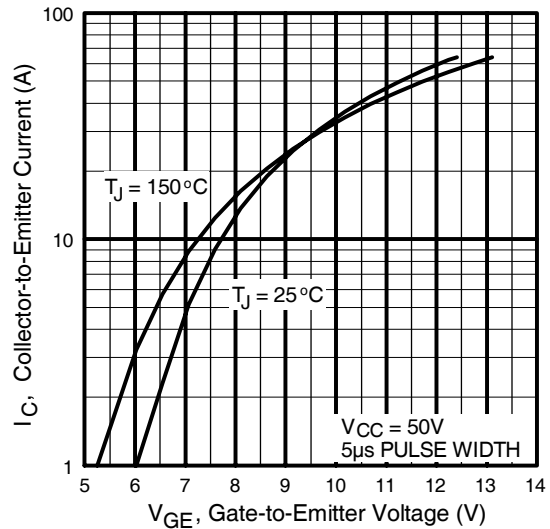
	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	27	40	nC	I <sub>C</sub> = 9.0A V <sub>CC</sub> = 400V See Fig. 8 V <sub>GE</sub> = 15V
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	4.2	6.2		
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	9.9	15		
t <sub>d(on)</sub>	Turn-On Delay Time	—	43	—	ns	T <sub>J</sub> = 25°C I <sub>C</sub> = 9.0A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 50Ω Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 18
t <sub>r</sub>	Rise Time	—	20	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	240	360		
t <sub>f</sub>	Fall Time	—	150	220		
E <sub>on</sub>	Turn-On Switching Loss	—	0.25	—	mJ	T <sub>J</sub> = 150°C, See Fig. 11, 18 I <sub>C</sub> = 9.0A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 50Ω Energy losses include "tail" and diode reverse recovery.
E <sub>off</sub>	Turn-Off Switching Loss	—	0.64	—		
E <sub>ts</sub>	Total Switching Loss	—	0.89	1.3		
t <sub>d(on)</sub>	Turn-On Delay Time	—	41	—	ns	Measured 5mm from package
t <sub>r</sub>	Rise Time	—	22	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	320	—		
t <sub>f</sub>	Fall Time	—	290	—		
E <sub>ts</sub>	Total Switching Loss	—	1.35	—	mJ	
L <sub>E</sub>	Internal Emitter Inductance	—	7.5	—	nH	
C <sub>ies</sub>	Input Capacitance	—	540	—	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V See Fig. 7 f = 1.0MHz
C <sub>oes</sub>	Output Capacitance	—	37	—		
C <sub>res</sub>	Reverse Transfer Capacitance	—	7.0	—		
t <sub>rr</sub>	Diode Reverse Recovery Time	—	37	55	ns	T <sub>J</sub> = 25°C See Fig. 14
		—	55	90		T <sub>J</sub> = 125°C
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	T <sub>J</sub> = 25°C See Fig. 15
		—	4.5	8.0		T <sub>J</sub> = 125°C
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	65	138	nC	T <sub>J</sub> = 25°C See Fig. 16
		—	124	360		T <sub>J</sub> = 125°C
di <sub>(rec)</sub> M/dt	Diode Peak Rate of Fall of Recovery During t <sub>b</sub>	—	240	—	A/μs	T <sub>J</sub> = 25°C See Fig. 17
		—	210	—		T <sub>J</sub> = 125°C



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

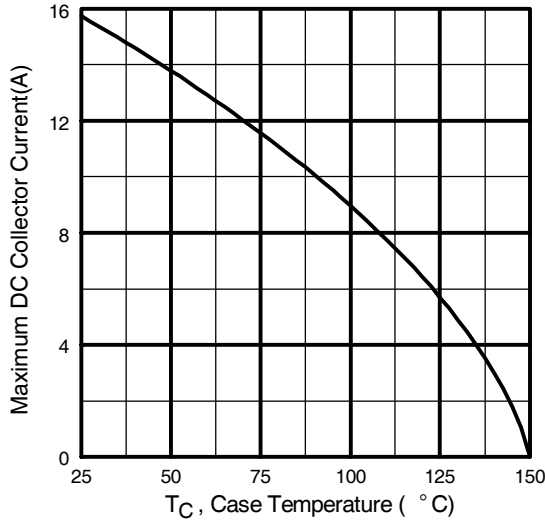


**Fig. 2 - Typical Output Characteristics**

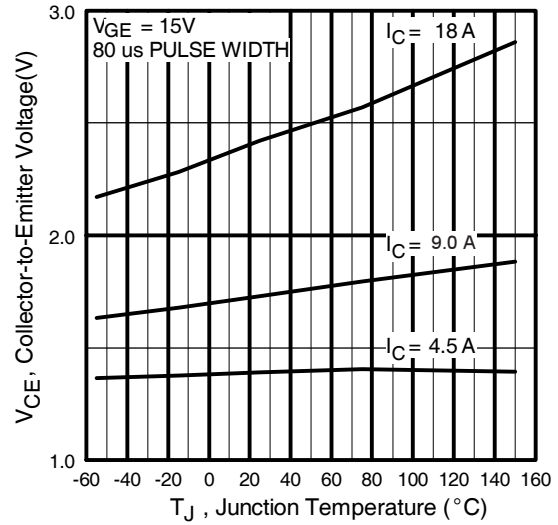


**Fig. 3 - Typical Transfer Characteristics**

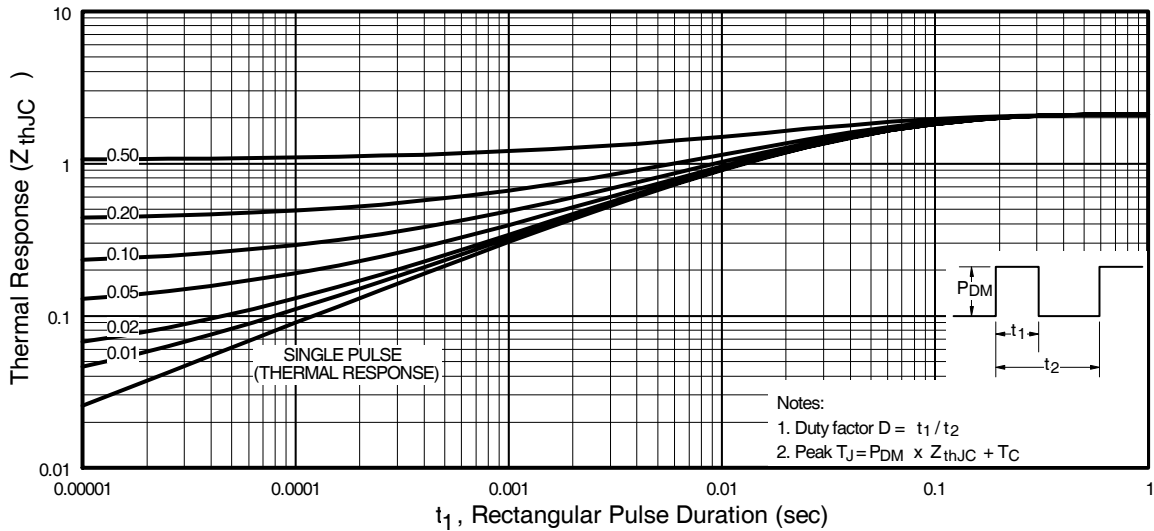
# IRG4BC20FDPbF



**Fig. 4 - Maximum Collector Current vs. Case Temperature**

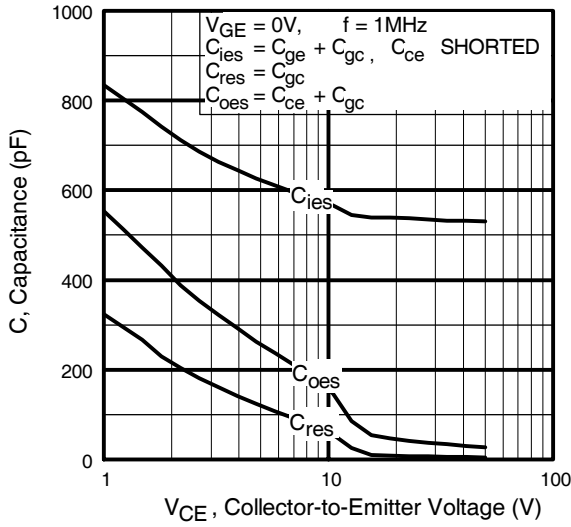


**Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature**

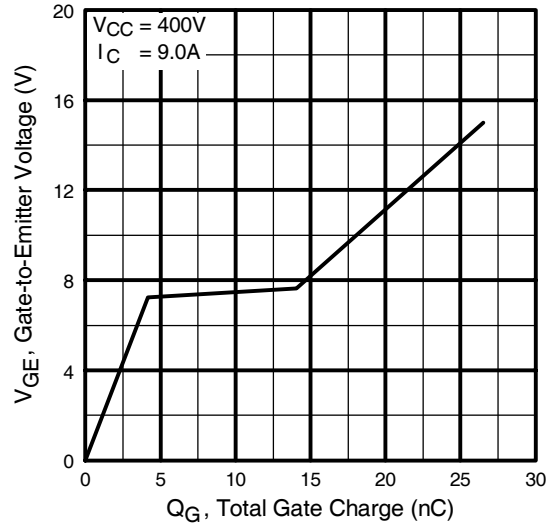


**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

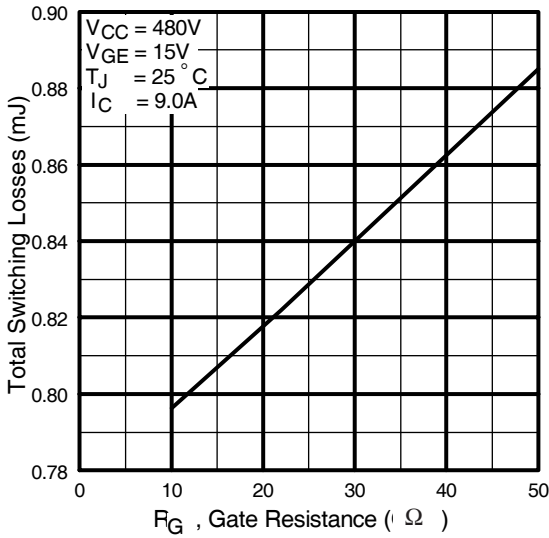
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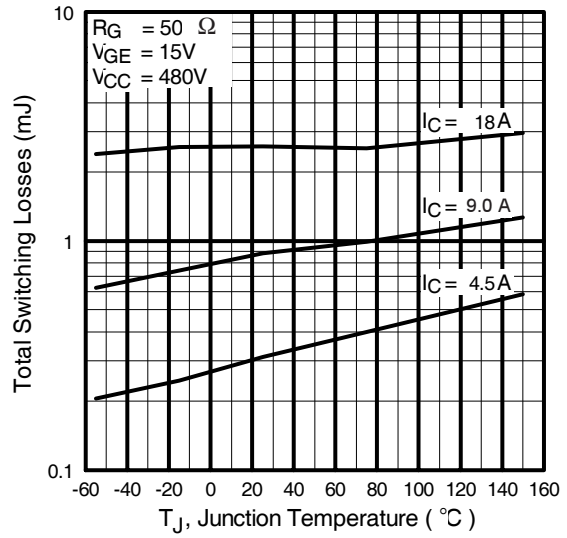
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

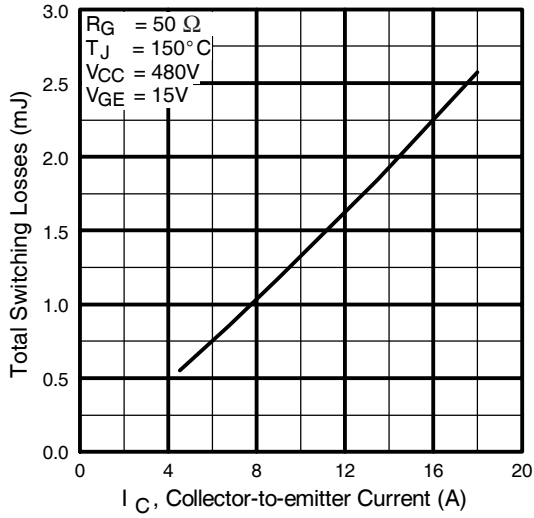


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

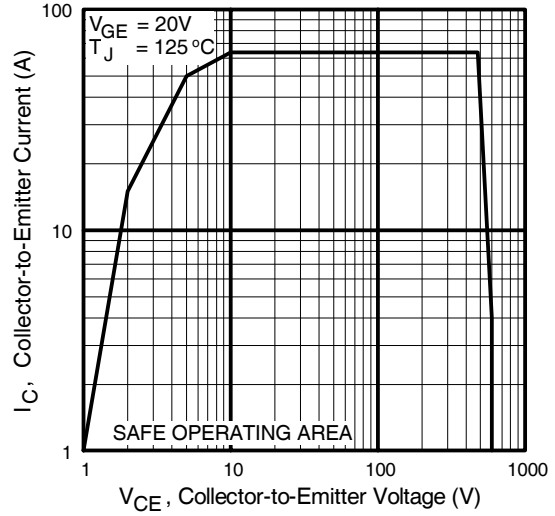


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

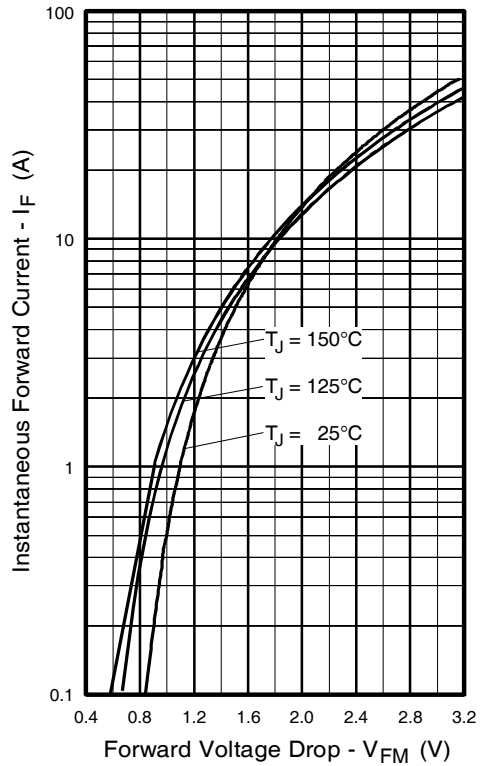
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**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

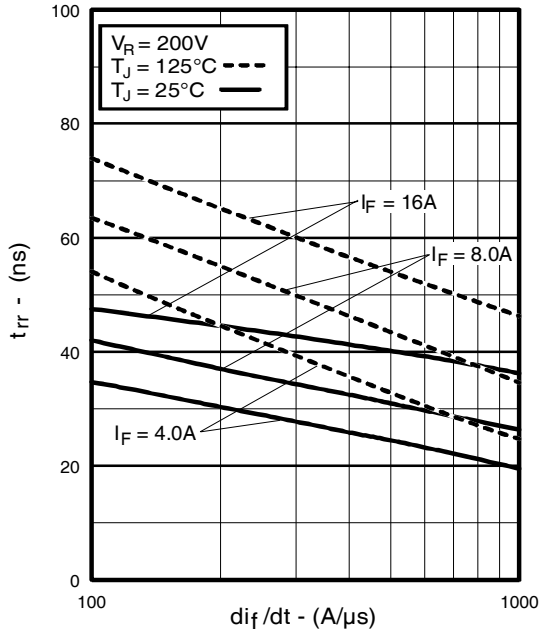


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

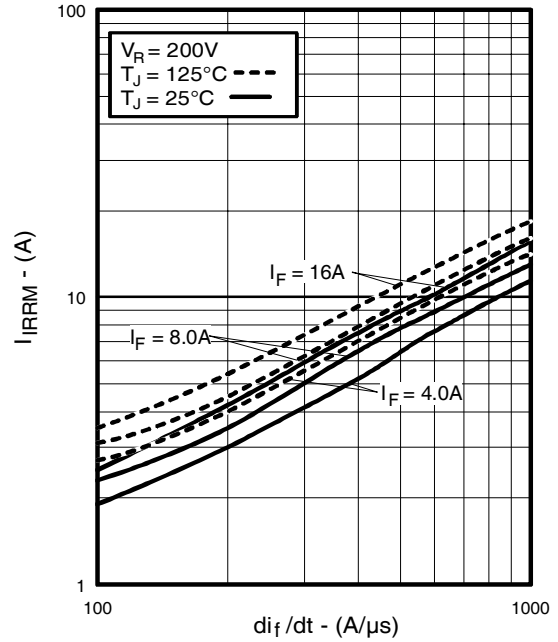


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

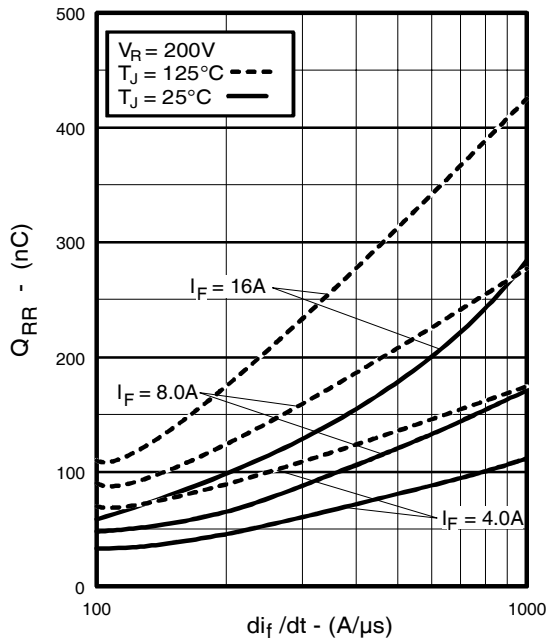


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

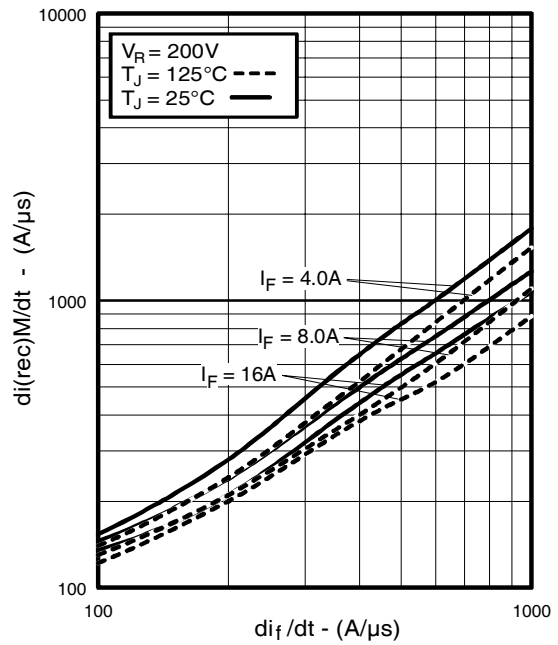
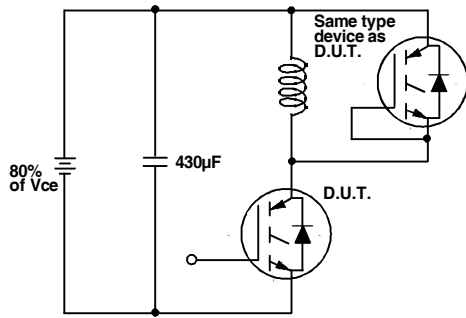
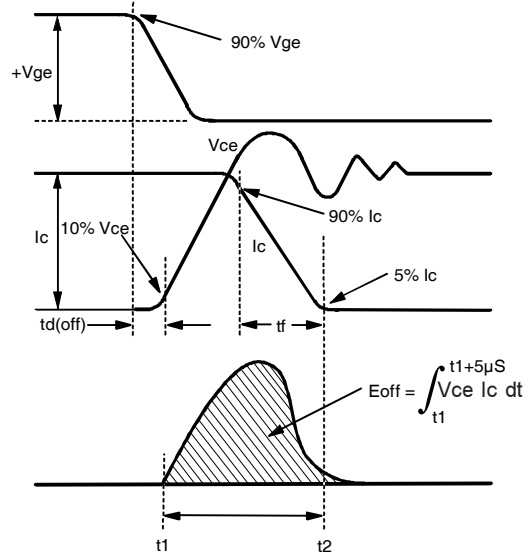


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$

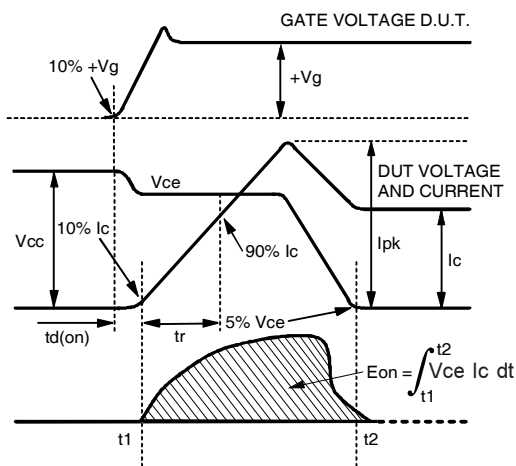
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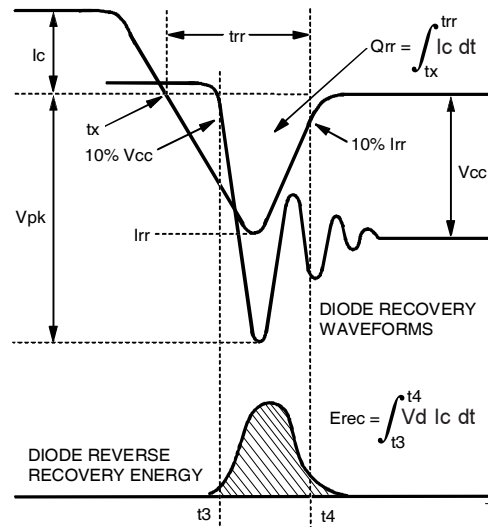
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



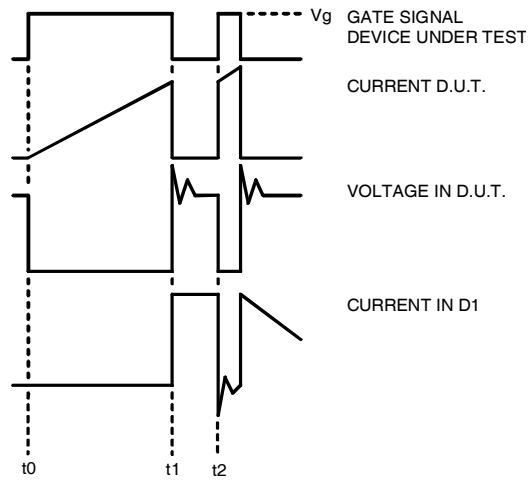


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit



Figure 19. Clamped Inductive Load Test Circuit

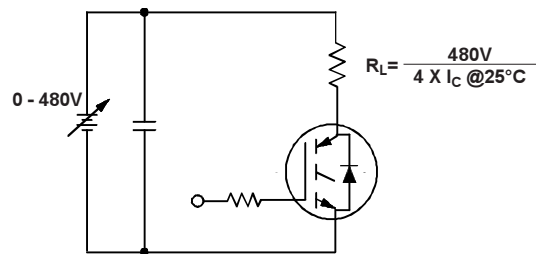


Figure 20. Pulsed Collector Current Test Circuit

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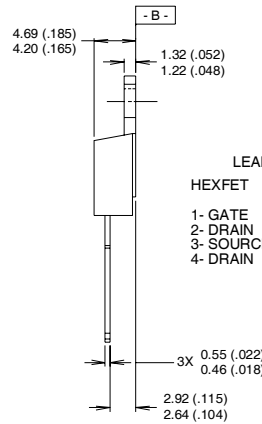
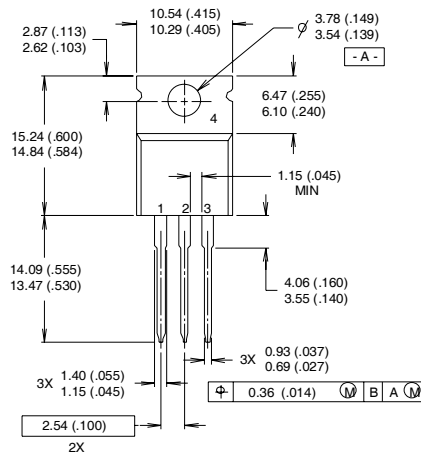
International  
**IR** Rectifier

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G = 50\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width 5.0 $\mu s$ , single shot.

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS	
HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

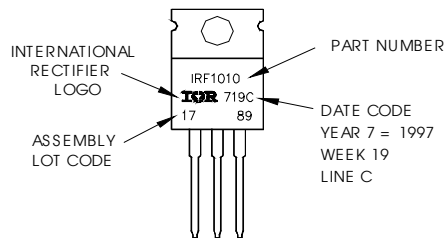
### NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
**IR** Rectifier

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 TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.12/03

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>